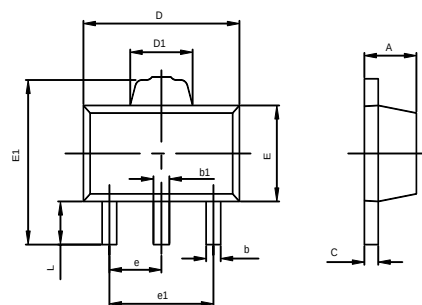


RoHS Compliant Product

Features

1. -60Volt V_{CEO}
2. 3 Amp continuous current
3. Low saturation voltage

SOT-89



Symbol	Dimensions in Millimeters		Dimensions in Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.360	0.560	0.014	0.022
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.400	1.800	0.055	0.071
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500TYP		0.060TYP	
e1	2.900	3.100	0.114	0.122
L	0.900	1.100	0.035	0.043

●Absolute maximum ratings ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	-80	V
Collector-emitter voltage	V_{CEO}	-60	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-3	A(DC)
		-6	A(Pulse)*1
Total power dissipation	P_C	0.5	W
		2	W *2
Junction temperature	T_J	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55~+150	$^\circ\text{C}$

*1 Single pulse, $P_w=10\text{ms}$

*2 When mounted on a $40\times 40\times 0.7$ mm ceramic board.

●Electrical characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-80	—	—	V	$I_C=-100\mu\text{A}$, $I_E=0$
Collector-emitter breakdown voltage	BV_{CEO}	-60	—	—	V	$I_C=-10\text{mA}$, $I_B=0$
Emitter-base breakdown voltage	BV_{EBO}	-5	—	—	V	$I_E=-100\mu\text{A}$, $I_C=0$
Collector cutoff current	I_{CBO}	—	—	0.1	μA	$V_{CB}=-60\text{V}$, $I_E=0$
Emitter cutoff current	I_{EBO}	—	—	0.1	μA	$V_{EB}=-4\text{V}$, $I_C=0$
Collector-emitter saturation voltage 1	$V_{CE(sat)1}$	—	-150	-300	mV	$I_C=-1\text{A}$, $I_B=-100\text{mA}$
Collector-emitter saturation voltage 2	$V_{CE(sat)2}$	—	-450	-600	mV	$I_C=-3\text{A}$, $I_B=-300\text{mA}$
Base-emitter saturation voltage Sat	$V_{BE(sat)}$	—	-0.9	-1.25	V	$I_C=-1\text{A}$, $I_B=-100\text{mA}$
Base-emitter saturation voltage On	$V_{BE(on)}$	—	-0.8	-1.0	V	$V_{CE}=-2\text{V}$, $I_C=-1\text{A}$
Output capacitance	C_{ob}	—	—	30	pF	$V_{CB}=-10\text{V}$, $I_E=0\text{A}$, $f=1\text{MHz}$
Current Gain - Bandwidth Product	f_T	100	140	—	MHz	$V_{CE}=-5\text{V}$, $I_C=-100\text{mA}$, $f=100\text{MHz}$
Switching Time	t_{on}	—	40	—	ns	$V_{CC}=-10\text{V}$, $I_C=-500\text{mA}$, $I_{B1}=I_{B2}=-50\text{mA}$
	t_{off}	—	450	—		
Current Gain	h_{FE1}	70	200	—		$V_{CE}=-2\text{V}$, $I_C=-50\text{mA}$
	h_{FE2}	100	200	300		$V_{CE}=-2\text{V}$, $I_C=-500\text{mA}$
	h_{FE3}	80	170	—		$V_{CE}=-2\text{V}$, $I_C=-1\text{A}$
	h_{FE4}	40	150	—		$V_{CE}=-2\text{V}$, $I_C=-2\text{A}$

Note: Measured under pulse condition. Pulse width<300us, Duty cycle<2%

Spice parameter data is available upon urquest for this device.

Electrical characteristics curves

